## SK30GB128



# SEMITOP<sup>®</sup> 2

**IGBT** Module

SK30GB128 SK30GAL128

SK30GAR128

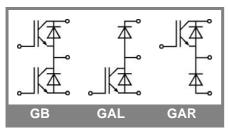
Preliminary Data

### Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB
- High short circuit capability
  SPT= Soft Punch Through technology
- V<sub>ce,sat</sub> with positive coefficient

#### **Typical Applications**

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



Absolute Maximum Ratings $T_s = 25 \text{ °C}$ , unless otherwise specified						
Symbol	Conditions		Values	Units		
IGBT	_			_		
V <sub>CES</sub>	T <sub>j</sub> = 25 °C T <sub>j</sub> = 125 °C		1200	V		
Ι <sub>C</sub>	T <sub>j</sub> = 125 °C	T <sub>s</sub> = 25 °C	35	А		
		T <sub>s</sub> = 80 °C	25	А		
I <sub>CRM</sub>	I <sub>CRM</sub> = 2 x I <sub>Cnom</sub>		50	А		
V <sub>GES</sub>			± 20	V		
t <sub>psc</sub>	V <sub>CC</sub> = 600 V; V <sub>GE</sub> ≤ 20 V; VCES < 1200 V	T <sub>j</sub> = 125 °C	10	μs		
Inverse	Diode		•			
I <sub>F</sub>	T <sub>j</sub> = 150 °C	T <sub>s</sub> = 25 °C	37	A		
		T <sub>s</sub> = 80 °C	25	А		
I <sub>FRM</sub>	I <sub>FRM</sub> = 2 x I <sub>Fnom</sub>			А		
I <sub>FSM</sub>	t <sub>p</sub> = 10 ms; half sine wave	T <sub>j</sub> = 150 °C	350	А		
Freewh	eeling Diode					
I <sub>F</sub>	T <sub>j</sub> = 150 °C	T <sub>case</sub> = 25 °C	37	A		
		T <sub>case</sub> = 80 °C	25	А		
I <sub>FRM</sub>				А		
I <sub>FSM</sub>	t <sub>p</sub> = 10 ms; half sine wave	T <sub>j</sub> = 150 °C	350	А		
Module						
I <sub>t(RMS)</sub>				А		
T <sub>vj</sub>			-40 +150	°C		
T <sub>stg</sub>			-40 +125	°C		
V <sub>isol</sub>	AC, 1 min.		2500	V		

Characteristics $T_s = 2$			25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units	
IGBT							
V <sub>GE(th)</sub>	$V_{GE} = V_{CE}, I_C = 1 \text{ mA}$		4,5	5,5	6,5	V	
I <sub>CES</sub>	$V_{GE}$ = 0 V, $V_{CE}$ = $V_{CES}$	T <sub>j</sub> = 25 °C		0,1	0,1	mA	
		T <sub>j</sub> = 125 °C				mA	
I <sub>GES</sub>	$V_{CE}$ = 0 V, $V_{GE}$ = 20 V	T <sub>j</sub> = 25 °C			200	nA	
		T <sub>j</sub> = 125 °C				nA	
V <sub>CE0</sub>		T <sub>j</sub> = 25 °C		1,1		V	
		T <sub>j</sub> = 125 °C		1		V	
r <sub>CE</sub>	V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25°C		36		mΩ	
		T <sub>j</sub> = 125°C		48		mΩ	
V <sub>CE(sat)</sub>	I <sub>Cnom</sub> = 25 A, V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25°C <sub>chiplev.</sub>	1,7	2	2,3	V	
		T <sub>j</sub> = 125°C <sub>chiplev</sub> .		2,2	3,7	V	
Cies				1,9		nF	
C <sub>oes</sub>	$V_{CE}$ = 25, $V_{GE}$ = 0 V	f = 1 MHz		0,16		nF	
C <sub>res</sub>				0,09		nF	
t <sub>d(on)</sub>				55		ns	
τ <sub>r</sub>	R <sub>Gon</sub> = 15 Ω	$V_{CC} = 600V$		26		ns	
E <sub>on</sub>	<b>D</b> (5.0	I <sub>C</sub> = 30A		2,8		mJ	
t <sub>d(off)</sub>	$R_{Goff}$ = 15 $\Omega$	T <sub>j</sub> = 125 °C		284		ns	
t <sub>f</sub>		V <sub>GE</sub> =±15V		40		ns	
E <sub>off</sub>				2,19		mJ	
R <sub>th(j-s)</sub>	per IGBT				1	K/W	

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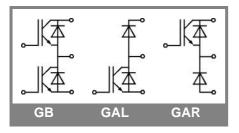
#### **Typical Applications**

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
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Characte	ristics					
Symbol	Conditions		min.	typ.	max.	Units
Inverse D						
V <sub>F</sub> = V <sub>EC</sub>	$I_{Fnom}$ = 25 A; $V_{GE}$ = 0 V	T <sub>j</sub> = 25 °C <sub>chiplev.</sub>		2	2,5	V
		T <sub>j</sub> = 125 °C <sub>chiplev.</sub>		1,8	2,3	V
V <sub>F0</sub>		T <sub>j</sub> = 125 °C		1	1,2	V
r <sub>F</sub>		T <sub>j</sub> = 125 °C		32	44	mΩ
I <sub>RRM</sub>	I <sub>F</sub> = 22 A	T <sub>i</sub> = 125 °C		25		Α
Q <sub>rr</sub>	di/dt = -500 A/µs			4,5		μC
E <sub>rr</sub>	V <sub>CC</sub> = 600V			1		mJ
R <sub>th(j-s)D</sub>	per diode				1,2	K/W
	eling Diode					
V <sub>F</sub> = V <sub>EC</sub>	I <sub>Fnom</sub> = 25 A; V <sub>GE</sub> = 0 V	T <sub>j</sub> = 25 °C <sub>chiplev.</sub>		2	2,5	V
		T <sub>j</sub> = 125 °C <sub>chiplev.</sub>		1,8	2,3	V
V <sub>F0</sub>		T <sub>j</sub> = 125 °C		1	1,2	V
r <sub>F</sub>		T <sub>j</sub> = 125 °C		32	44	V
I <sub>RRM</sub>	I <sub>F</sub> = 22 A	T <sub>i</sub> = 125 °C		253		Α
Q <sub>rr</sub>	di/dt = -500 A/µs	,		4,5		μC
E <sub>rr</sub>	V <sub>R</sub> =600V			1		mJ
	per diode				1,2	K/W
M <sub>s</sub>	to heat sink M1				2	Nm
w				19		g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.



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